

# Keita Tachiki

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Body doping dependence of field-effect mobility in both n- and p-channel 4H-SiC metal-oxide-semiconductor field-effect transistors with nitrated gate oxides. Applied Physics Express, 2022, 15, 036503.	1.1	4
2	Mobility enhancement in heavily doped 4H-SiC (0001), (112̄,0), and (11̄,00) MOSFETs via an oxidation-minimizing process. Applied Physics Express, 2022, 15, 071001.	1.1	9
3	Mobility improvement of 4H-SiC (0001) MOSFETs by a three-step process of H <sub>2</sub> etching, SiO <sub>2</sub> deposition, and interface nitridation. Applied Physics Express, 2021, 14, 031001.	1.1	42
4	Improvement of Both n- and p-Channel Mobilities in 4H-SiC MOSFETs by High-Temperature N <sub>2</sub> Annealing. IEEE Transactions on Electron Devices, 2021, 68, 638-644.	1.6	19
5	Short-Channel Effects in SiC MOSFETs Based on Analyses of Saturation Drain Current. IEEE Transactions on Electron Devices, 2021, 68, 1382-1384.	1.6	17
6	Design and formation of SiC (0001)/SiO <sub>2</sub> interfaces via Si deposition followed by low-temperature oxidation and high-temperature nitridation. Applied Physics Express, 2020, 13, 091003.	1.1	38
7	Formation of high-quality SiC(0001)/SiO <sub>2</sub> structures by excluding oxidation process with H <sub>2</sub> etching before SiO <sub>2</sub> deposition and high-temperature N <sub>2</sub> annealing. Applied Physics Express, 2020, 13, 121002.	1.1	25
8	Reduction of interface state density in SiC (0001) MOS structures by low-oxygen-partial-pressure annealing. Applied Physics Express, 2019, 12, 031001.	1.1	15
9	Estimation of Threshold Voltage in SiC Short-Channel MOSFETs. IEEE Transactions on Electron Devices, 2018, 65, 3077-3080.	1.6	28